Description

JMT P-channel Enhancement Mode Power MosFET

Features

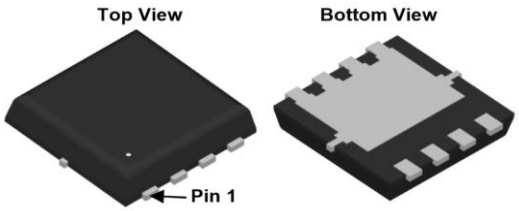
- -30V, -12A
  $R_{DS(ON)}$ < 17.4mΩ @ V_{GS} = -10V
  $R_{DS(ON)}$ < 23mΩ @ V_{GS} = -4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free

Applications

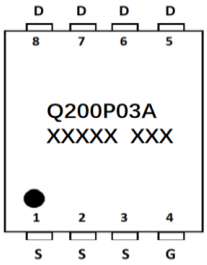
- Load Switch
- PWM Application
- Power Management

100% UIS TESTED!
100% ΔVds TESTED!

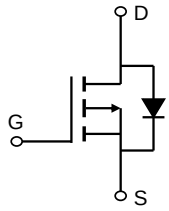
RoHS



PDFN3x3-8L



Marking and Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
Q200P03A	JMTQ200P03A-P	TAPING	PDFN3x3-8L	13"	5000	50000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		-30	V
V_{GS}	Gate-to-Source Voltage		±25	V
I_D	Continuous Drain Current	T_C = 25°C	-12	A
		T_C = 100°C	-8	
I_{DM}	Pulsed Drain Current (1)		-48	A
E_{AS}	Single Pulsed Avalanche Energy (2)		7.8	mJ
P_D	Power Dissipation	T_C = 25°C	30	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)		46	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		4.1	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = -250μA, V_{GS} = 0V	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -30V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±25V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250μA	-1.0	-1.6	-2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = -10V, I_D = -10A	-	13.4	17.4	mΩ
		V_{GS} = -4.5V, I_D = -5A	-	17.7	23.0	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = -15V, f = 1MHz	-	1267	-	pF
C_{oss}	Output Capacitance		-	166	-	pF
C_{rss}	Reverse Transfer Capacitance		-	126	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to -10V V_{DS} = -15V, I_D = -5A	-	23	-	nC
Q_{gs}	Gate Source Charge		-	4	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = -10V, V_{DD} = -15V I_D= -5A, R_{GEN} = 3Ω	-	4	-	ns
t_r	Turn-On Rise Time		-	3	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	60	-	ns
t_f	Turn-Off Fall Time		-	50	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-12	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-48	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = -12A	-	-	-1.2	V
trr	Body Diode Reverse Recovery Time	I_F = -5A, di/dt = 100A/us	-	12	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	4	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2.EAS condition: Starting T_J=25C, V_{DD}=-15V, V_G=-10V, R_G=25ohm, L=0.5mH, I_{AS}=-8A

3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB

4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Output Characteristics

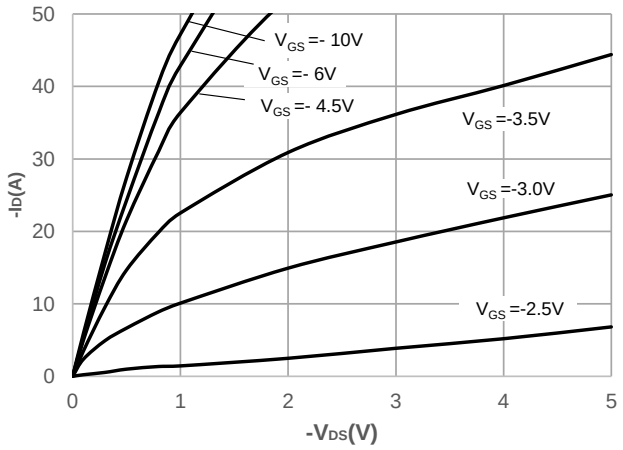


Figure 2: Typical Transfer Characteristics

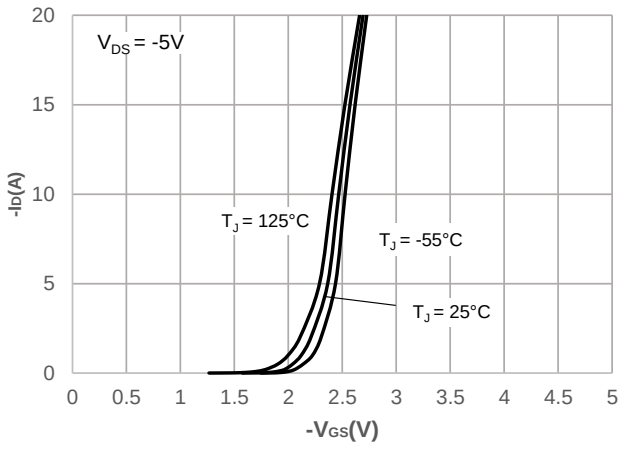


Figure 3: On-resistance vs. Drain Current

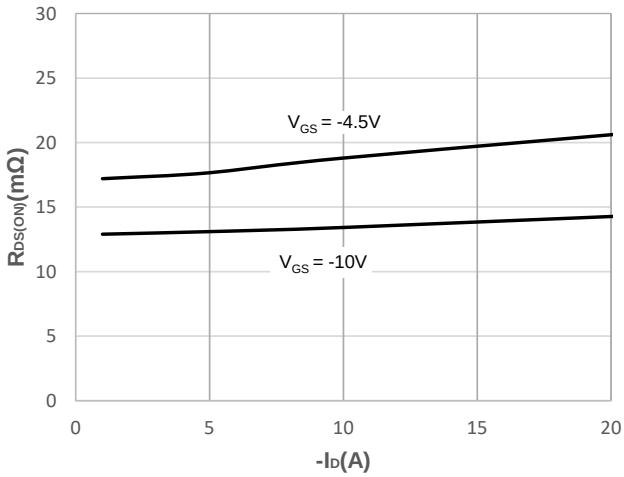


Figure 4: Body Diode Characteristics

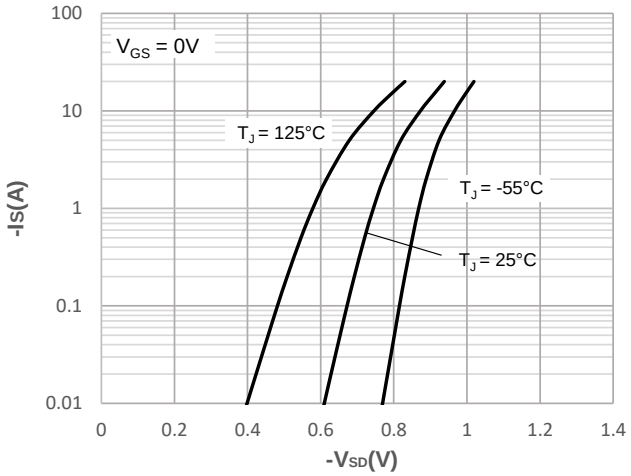


Figure 5: Gate Charge Characteristics

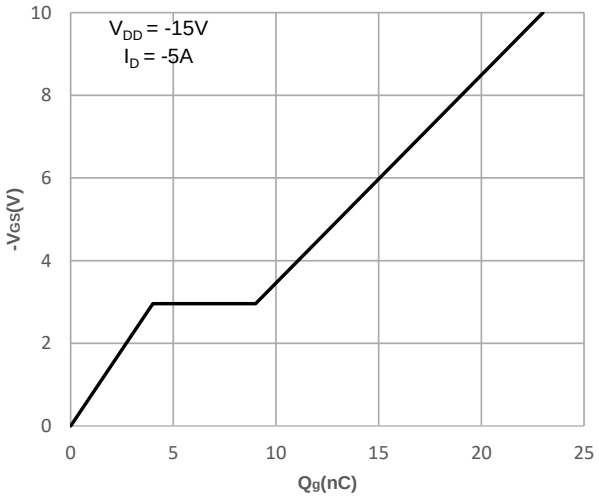
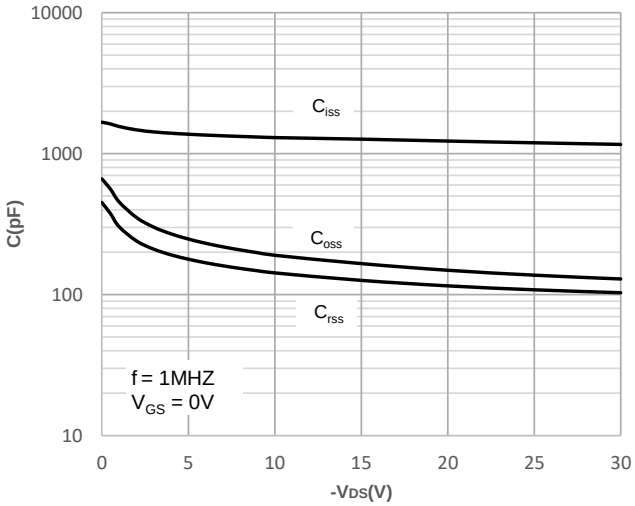


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

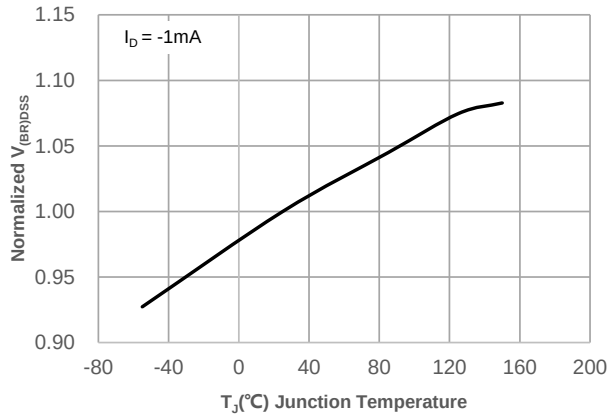


Figure 8: Normalized on Resistance vs. Junction Temperature

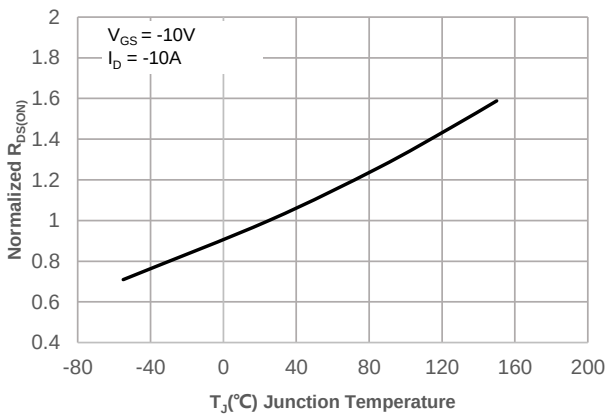


Figure 9: Maximum Safe Operating Area

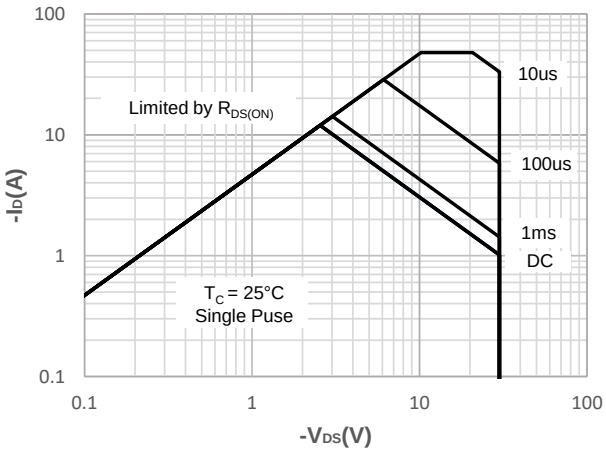


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

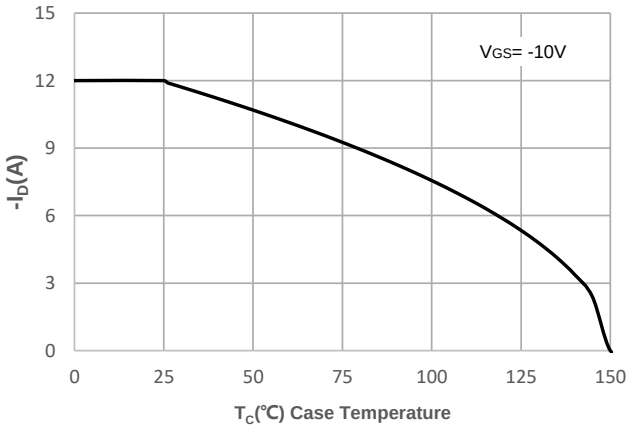


Figure 11: Normalized Maximum Transient Thermal Impedance

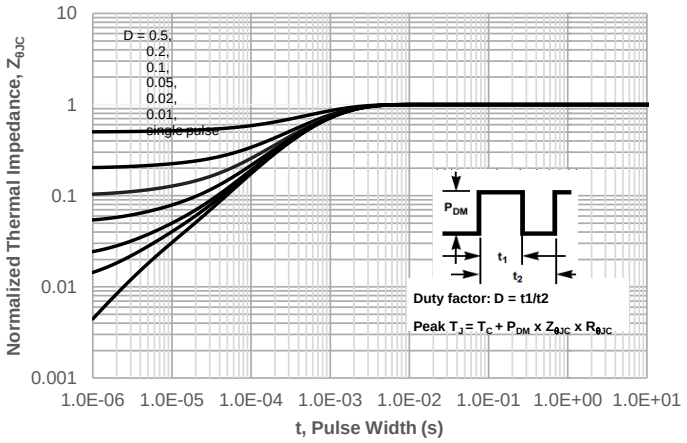
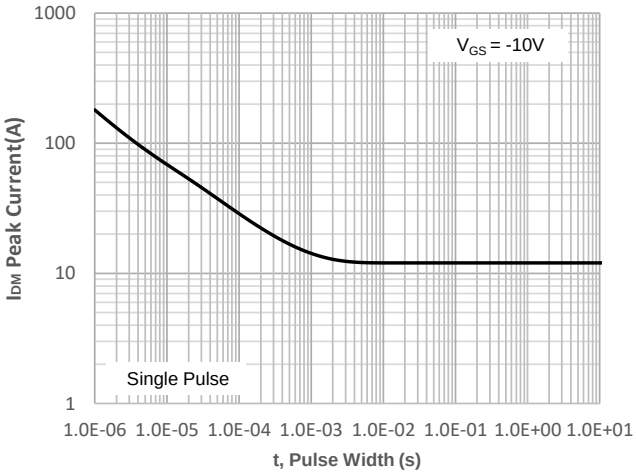


Figure 12: Peak Current Capacity



Test Circuit

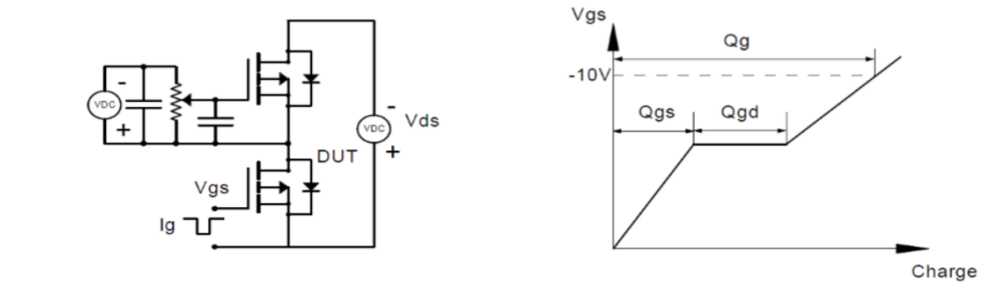


Figure 1: Gate Charge Test Circuit & Waveform

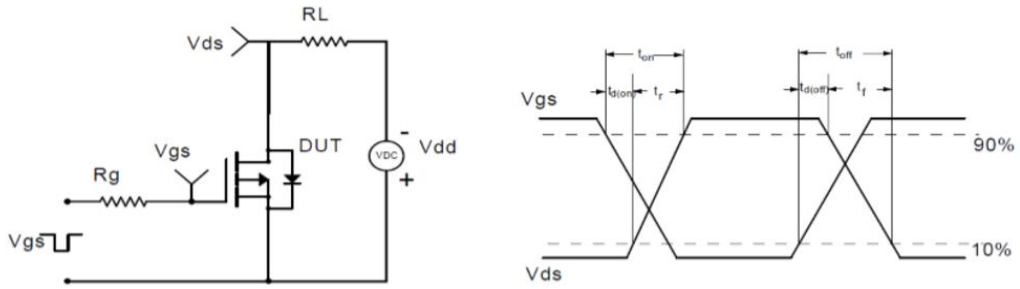


Figure 2: Resistive Switching Test Circuit & Waveform

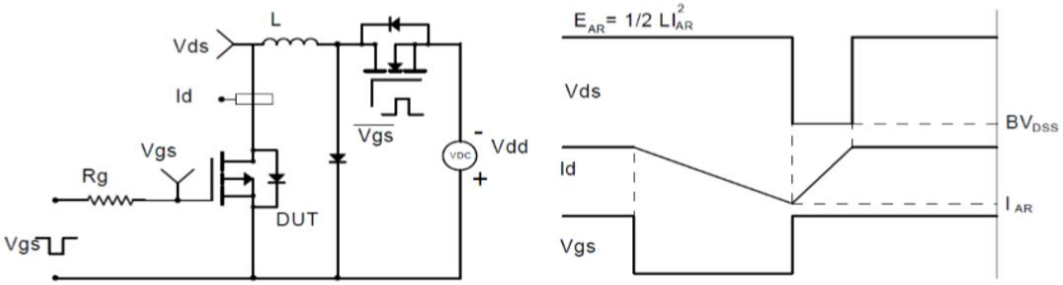


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

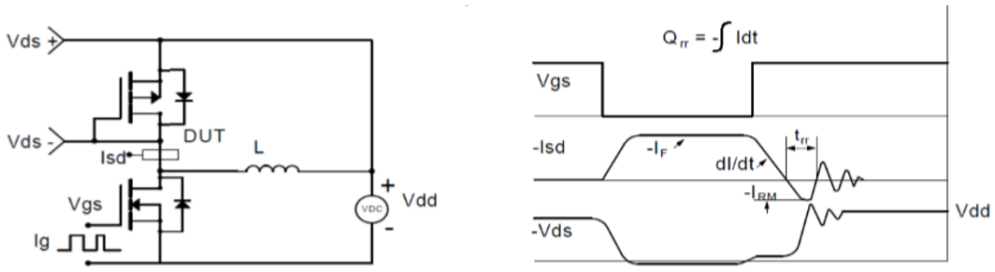
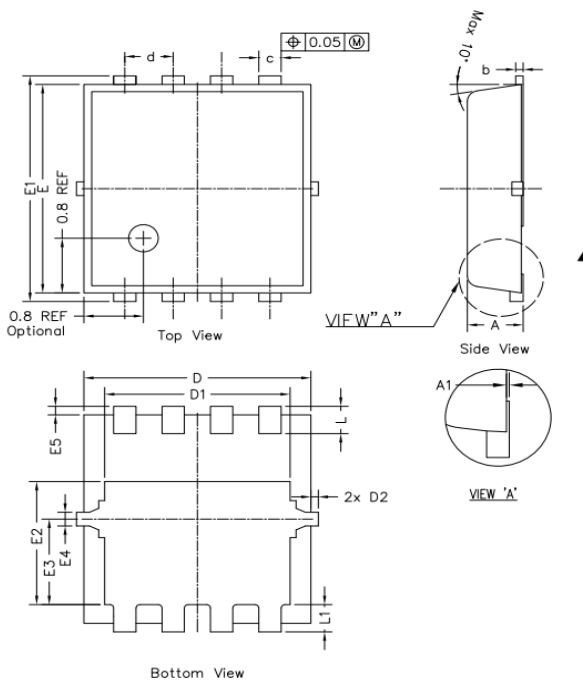


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN3x3-8L)



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	---	---	0.050	----	----	0.002
b	0.144	0.152	0.202	0.006	0.006	0.008
c	0.250	0.300	0.350	0.010	0.012	0.014
d	0.65 BSC			0.026 BSC		
D	2.950	3.050	3.150	0.116	0.120	0.124
D1	2.390	2.490	2.590	0.094	0.098	0.102
D2	---	---	0.125	---	---	0.005
E	2.950	3.050	3.150	0.116	0.120	0.124
E1	3.200	3.300	3.400	0.126	0.130	0.134
E2	1.700	1.800	1.900	0.067	0.071	0.075
E3	1.150	1.250	1.350	0.045	0.049	0.053
E4	0.150	0.200	0.250	0.006	0.008	0.010
E5	0.075	0.125	0.175	0.003	0.005	0.007
L	0.300	0.400	0.500	0.01	0.02	0.02
L1	0.300	0.400	0.500	0.01	0.02	0.02

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